

**N- AND P-Channel Enhancement Mode MOSFET**

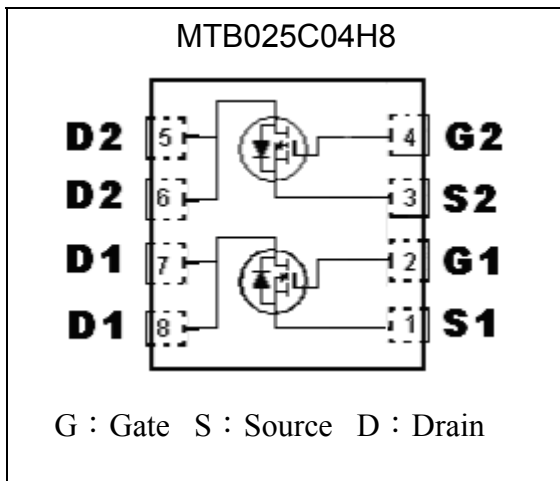
# MTB025C04H8

	N-CH	P-CH
BV <sub>DSS</sub>	40V	-40V
I <sub>D</sub> @V <sub>GS</sub> =10V(-10V), T <sub>A</sub> =25°C	7.3A	-6.6A
I <sub>D</sub> @V <sub>GS</sub> =10V(-10V), T <sub>C</sub> =25°C	21A	-19A
R <sub>DS(on)(typ)</sub> @V <sub>GS</sub> =10V(-10V)	18.3mΩ	28.3mΩ
R <sub>DS(on)(typ)</sub> @V <sub>GS</sub> =4.5V(-4.5V)	26.6mΩ	41.3mΩ

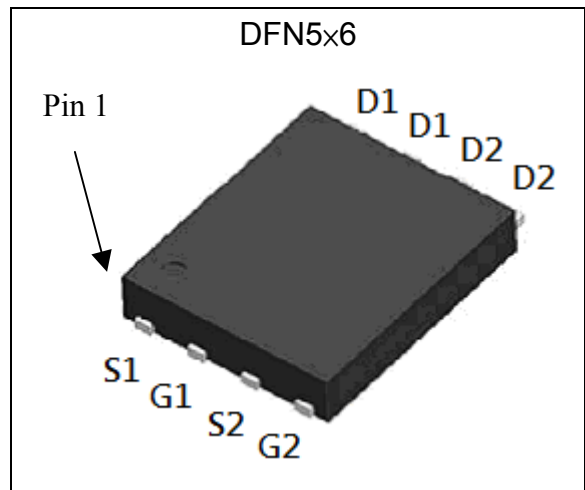
**Features**

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Pb-free lead plating and halogen-free package

**Equivalent Circuit**

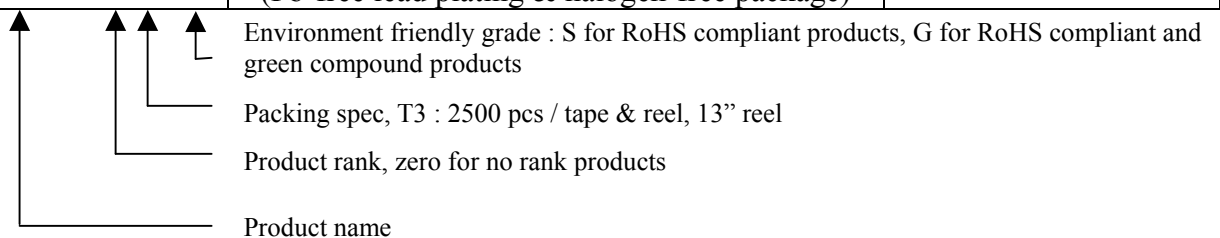


**Outline**



**Ordering Information**

Device	Package	Shipping
MTB025C04H8-0-T6-G	DFN 5 × 6 (Pb-free lead plating & halogen-free package)	3000 pcs / Tape & Reel





**Absolute Maximum Ratings** (T<sub>C</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Limits		Unit	
		N-channel	P-channel		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	-40	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	±20		
Continuous Drain Current	T <sub>A</sub> =25 °C, V <sub>GS</sub> =10V (-10V)	I <sub>DSM</sub>	7.3	A	
	T <sub>A</sub> =70 °C, V <sub>GS</sub> =10V (-10V)		5.8		
	T <sub>C</sub> =25 °C, V <sub>GS</sub> =10V (-10V)	I <sub>D</sub>	21		
	T <sub>C</sub> =100 °C, V <sub>GS</sub> =10V (-10V)		13.3		
Pulsed Drain Current (Note 1 & 2)	I <sub>DM</sub>	40	-40		
Power Dissipation	T <sub>A</sub> =25 °C	P <sub>DSM</sub>	2.5 (Note 3)		W
	T <sub>A</sub> =70 °C		1.6 (Note 3)		
	T <sub>C</sub> =25 °C	P <sub>D</sub>	21		
	T <sub>C</sub> =100 °C		8.4		
Operating Junction and Storage Temperature Range	T <sub>j</sub> ; T <sub>stg</sub>	-55~+150		°C	

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R <sub>th,j-c</sub>	6	°C/W
Thermal Resistance, Junction-to-ambient, max	R <sub>th,j-a</sub>	50 (Note 3)	

- Note : 1. Pulse width limited by maximum junction temperature  
 2. Duty cycle ≤ 1%  
 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board, t ≤ 10s; 125°C/W when mounted on minimum copper pad.

**N-Channel Electrical Characteristics** (T<sub>C</sub>=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	40	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	1.0	-	2.5		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V
	-	-	25		V <sub>DS</sub> =32V, V <sub>GS</sub> =0, T <sub>j</sub> =125°C
*R <sub>DS(ON)</sub>	-	18.3	26	mΩ	I <sub>D</sub> =12A, V <sub>GS</sub> =10V
	-	26.6	35		I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V
*G <sub>FS</sub>	-	5.4	-	S	V <sub>DS</sub> =10V, I <sub>D</sub> =7A
<b>Dynamic</b>					
C <sub>iss</sub>	-	570	855	pF	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz
C <sub>oss</sub>	-	45	-		
C <sub>rss</sub>	-	40	-		
*t <sub>d(ON)</sub>	-	7.2	-	ns	V <sub>DS</sub> =20V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>G</sub> =6 Ω
*t <sub>r</sub>	-	17	-		
*t <sub>d(OFF)</sub>	-	24.8	-		
*t <sub>f</sub>	-	7.4	-		



*Qg	-	6	9	nC	V <sub>DS</sub> =25V, I <sub>D</sub> =5A, V <sub>GS</sub> =4.5V
*Qgs	-	2.4	-		
*Qgd	-	2.2	-		
<b>Body Diode</b>					
*V <sub>SD</sub>	-	0.75	1	V	V <sub>GS</sub> =0V, I <sub>S</sub> =1A
*trr	-	6.3	-	ns	I <sub>F</sub> =5A dI <sub>F</sub> /dt=100A/μs
*Qrr	-	2.4	-	nC	

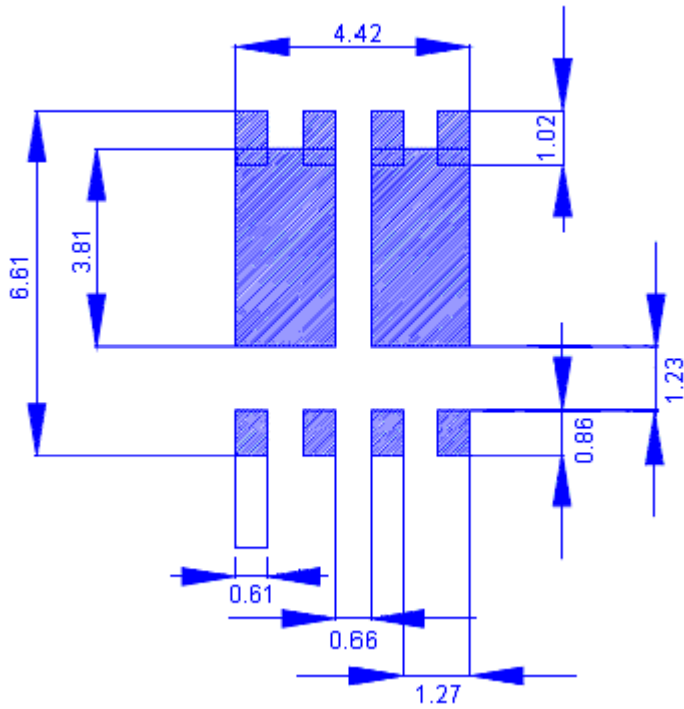
\*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

**P-Channel Electrical Characteristics (T<sub>c</sub>=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	-40	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA
V <sub>GS(th)</sub>	-1.0	-	-2.5		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V
	-	-	-25		V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V, T <sub>j</sub> =125°C
*R <sub>DS(ON)</sub>	-	28.3	37	mΩ	I <sub>D</sub> =-12A, V <sub>GS</sub> =-10V
	-	41.3	54		I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V
*G <sub>FS</sub>	-	8.4	-	S	V <sub>DS</sub> =-10V, I <sub>D</sub> =-5A
<b>Dynamic</b>					
C <sub>iss</sub>	-	971	1457	pF	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHz
C <sub>oss</sub>	-	80	-		
C <sub>rss</sub>	-	66	-		
*td(ON)	-	7.8	-	ns	V <sub>DS</sub> =-20V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω
*tr	-	17.6	-		
*td(OFF)	-	61.2	-		
*tf	-	24	-		
*Qg	-	10	15	nC	V <sub>DS</sub> =-25V, I <sub>D</sub> =-4.9A, V <sub>GS</sub> =-4.5V
*Qgs	-	3.2	-		
*Qgd	-	3.8	-		
<b>Body Diode</b>					
*V <sub>SD</sub>	-	-0.75	-1	V	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A
*trr	-	8.8	-	ns	I <sub>F</sub> =-5A dI <sub>F</sub> /dt=100A/μs
*Qrr	-	3.6	-	nC	

\*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

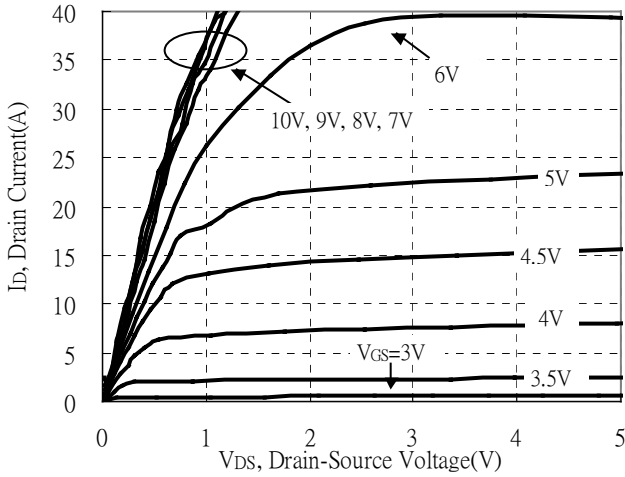
### Recommended Soldering Footprint



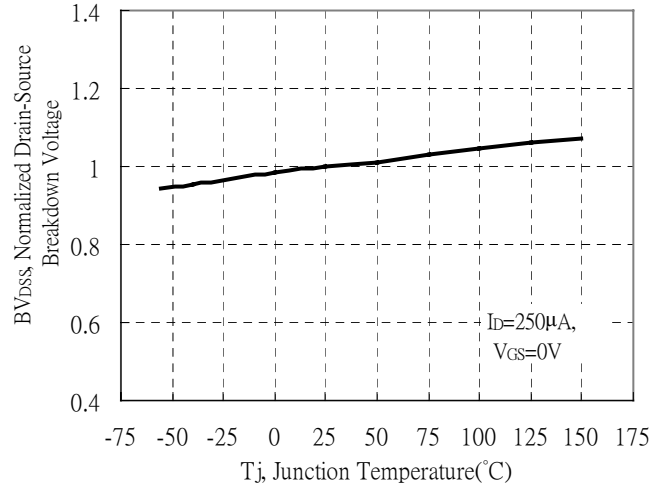
unit : mm

**Typical Characteristics : Q1( N-channel )**

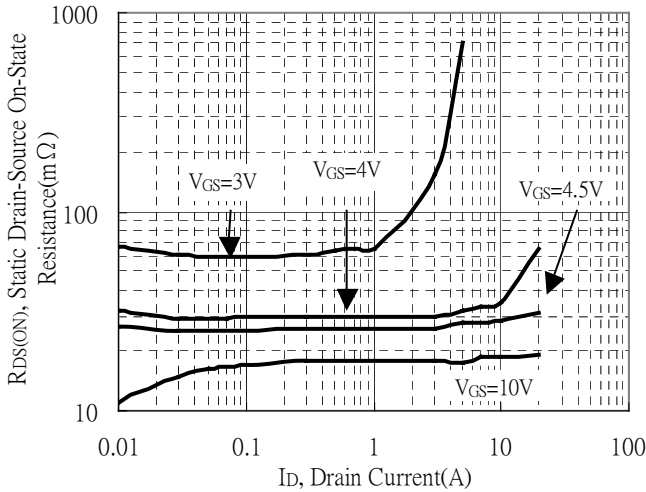
Typical Output Characteristics



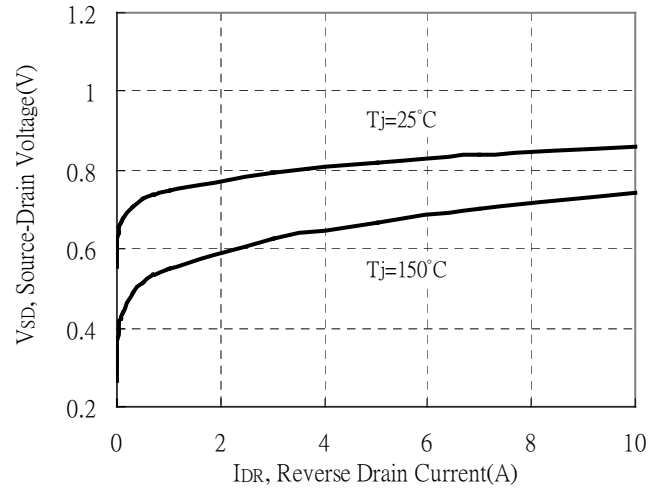
Brekdown Voltage vs Ambient Temperature



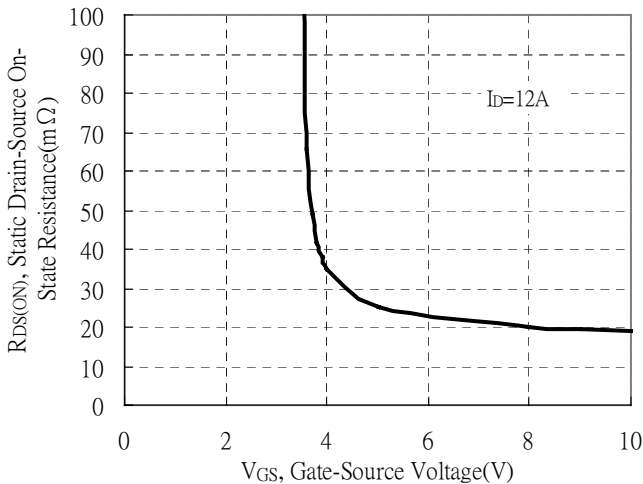
Static Drain-Source On-State resistance vs Drain Current



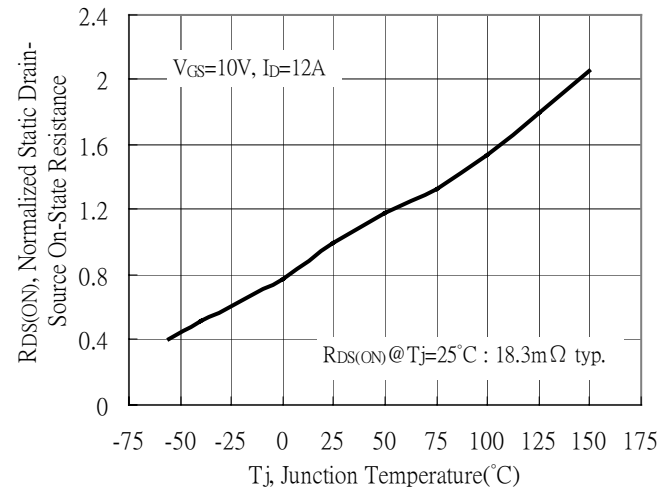
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

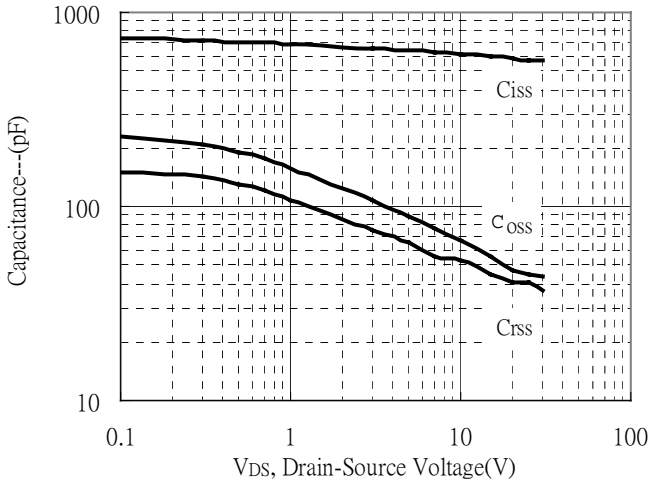


Drain-Source On-State Resistance vs Junction Temperature

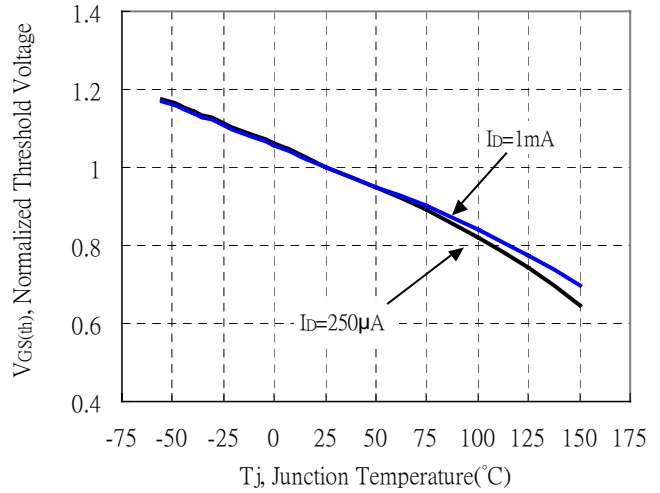


**Typical Characteristics(Cont.) : Q1( N-channel)**

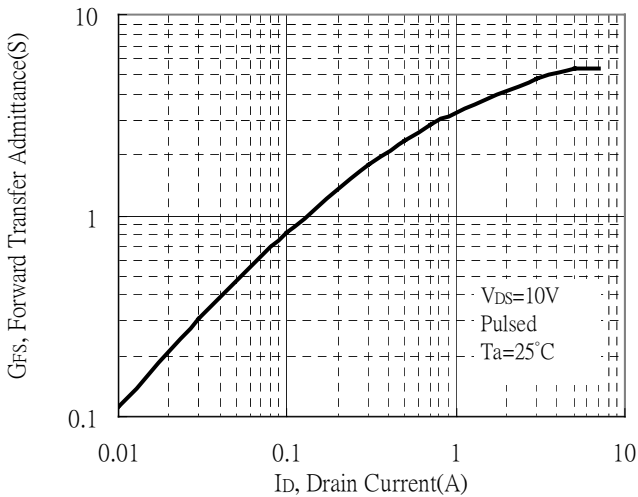
Capacitance vs Drain-to-Source Voltage



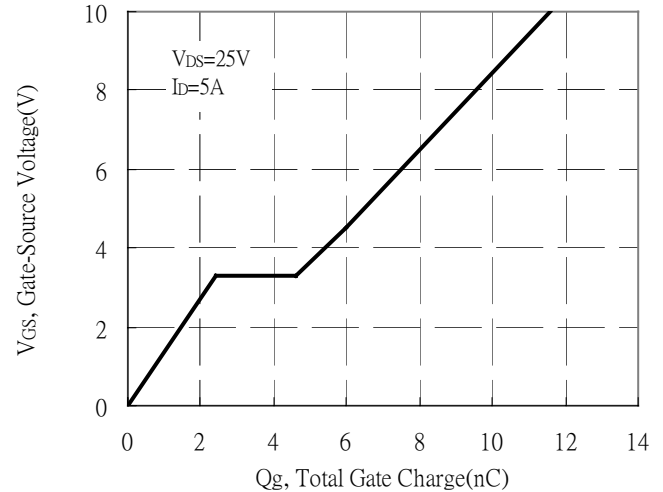
Threshold Voltage vs Junction Temperature



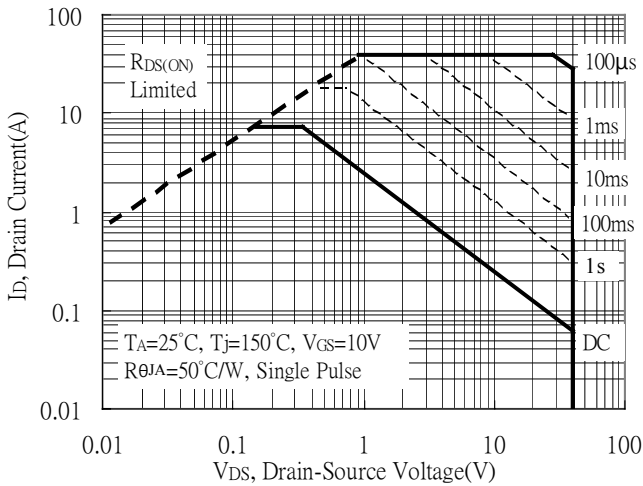
Forward Transfer Admittance vs Drain Current



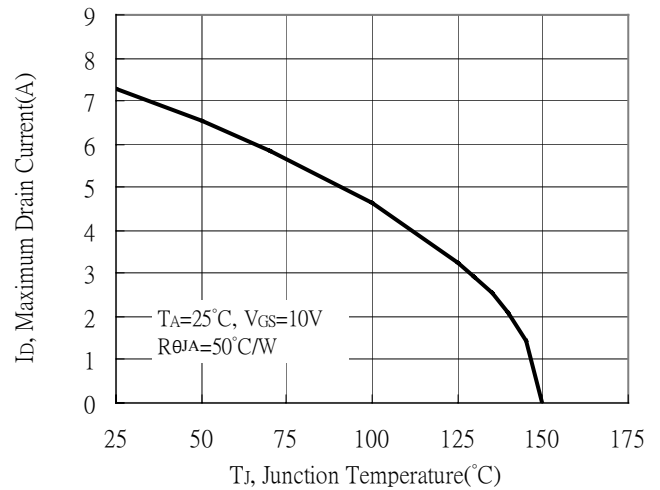
Gate Charge Characteristics



Maximum Safe Operating Area



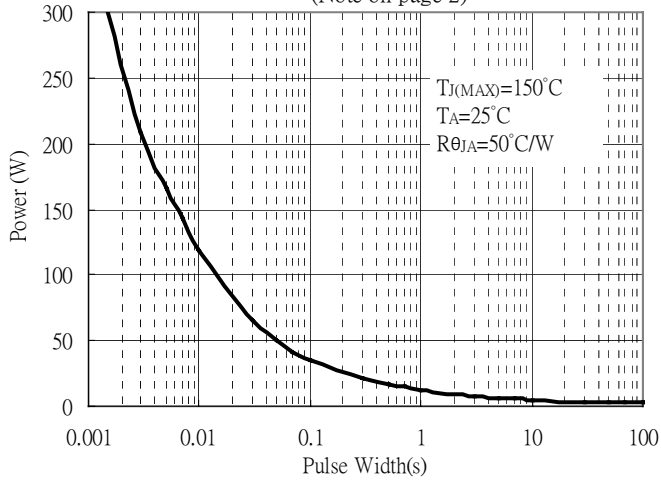
Maximum Drain Current vs Junction Temperature



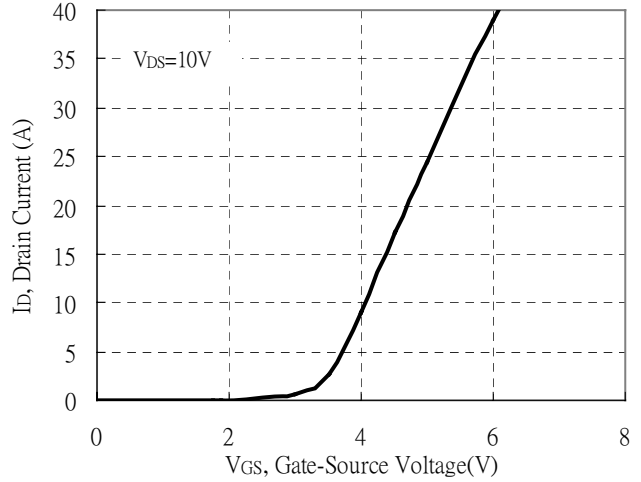


**Typical Characteristics(Cont.) : Q1( N-channel)**

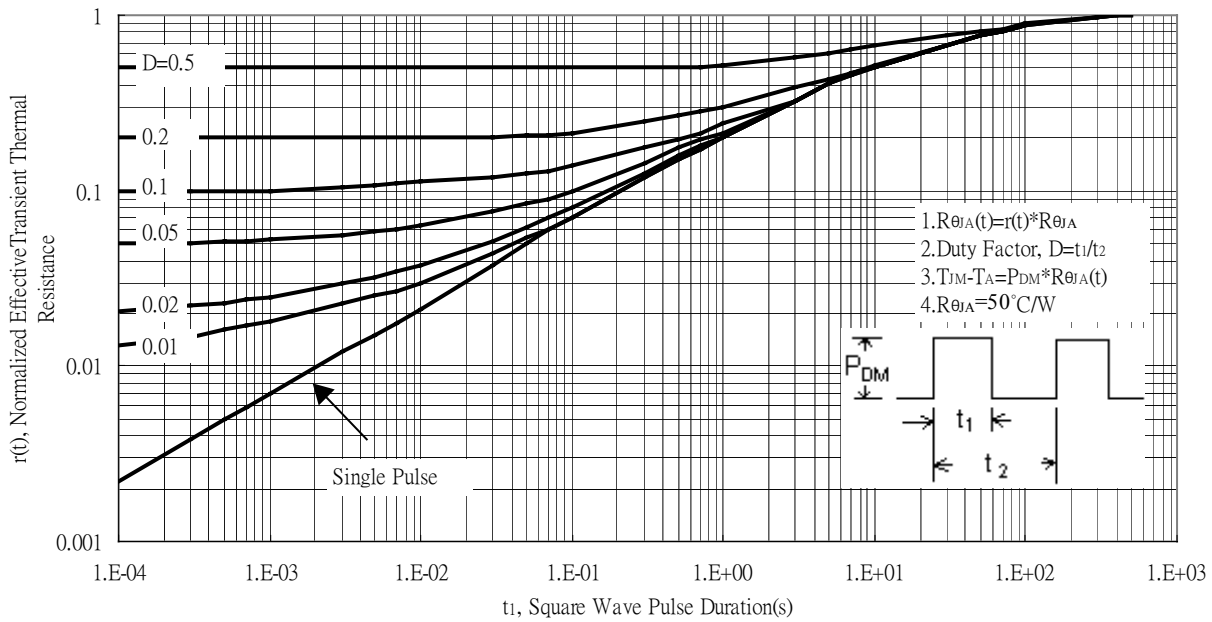
Single Pulse Power Rating, Junction to Ambient  
 (Note on page 2)



Typical Transfer Characteristics

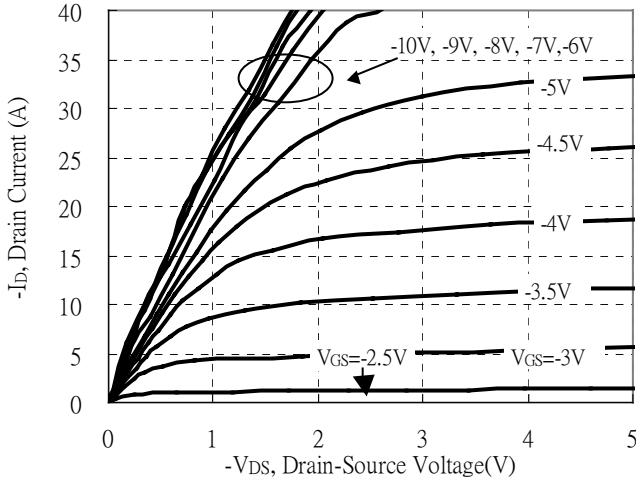


Transient Thermal Response Curves

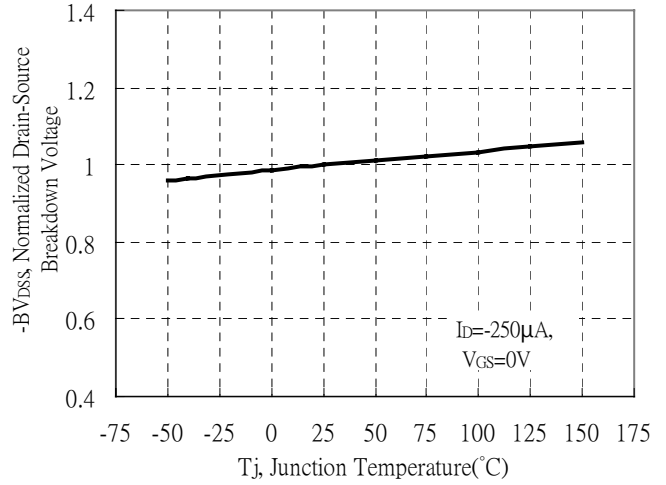


**Typical Characteristics : Q2( P-channel)**

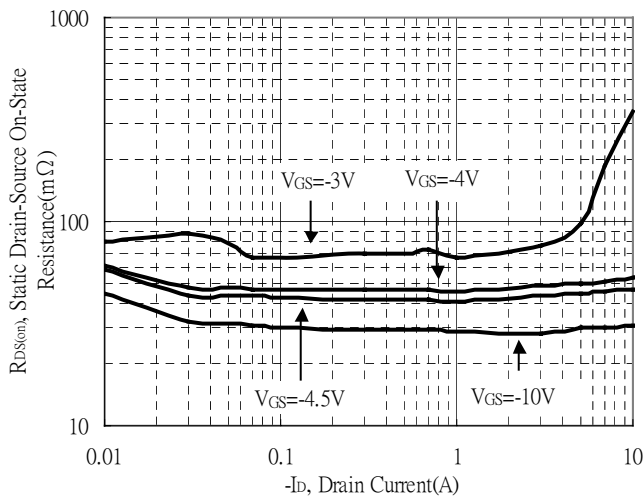
Typical Output Characteristics



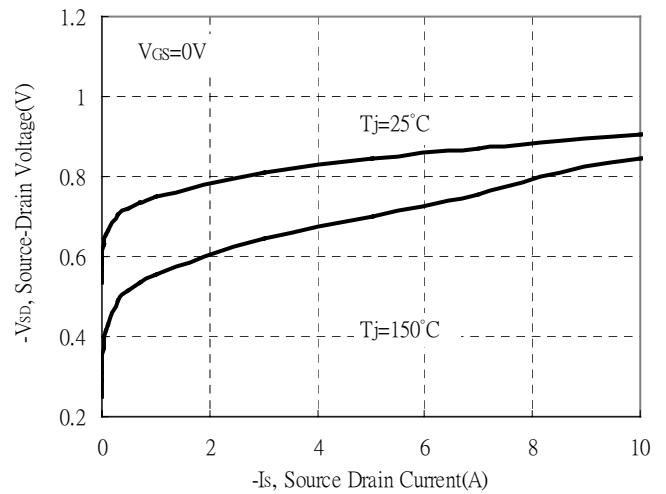
Breakdown Voltage vs Ambient Temperature



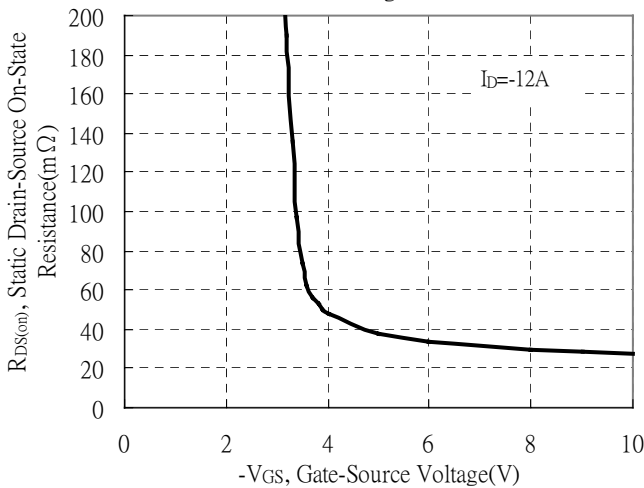
Static Drain-Source On-State resistance vs Drain Current



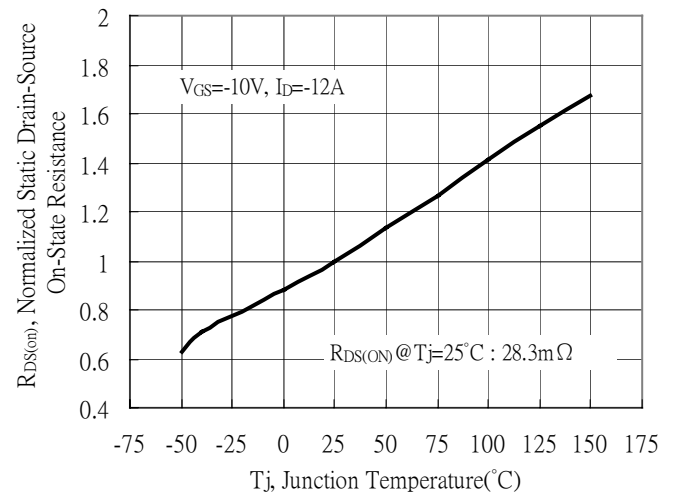
Source Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage



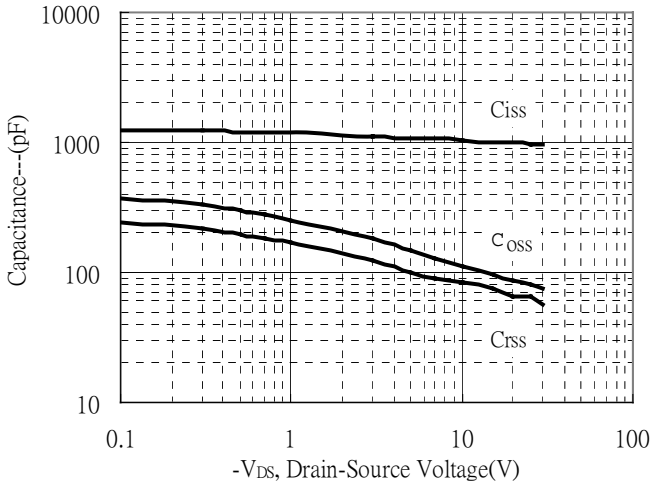
Drain-Source On-State Resistance vs Junction Temperature



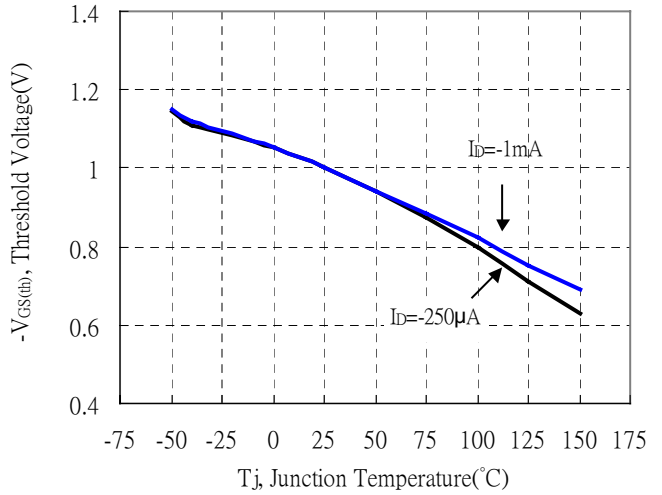


**Typical Characteristics(Cont.) : Q2(P-channel)**

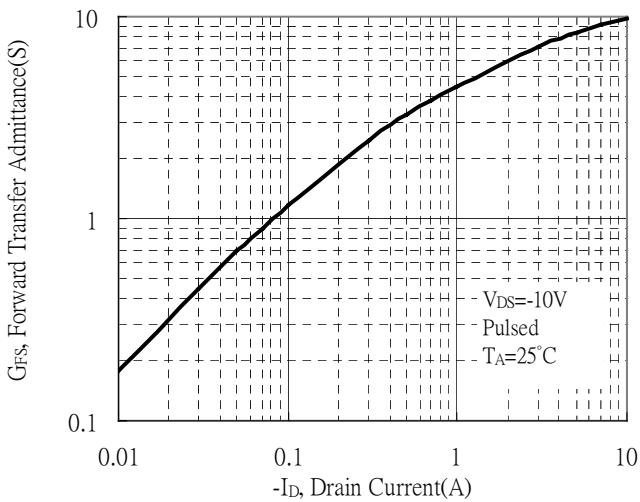
Capacitance vs Drain-to-Source Voltage



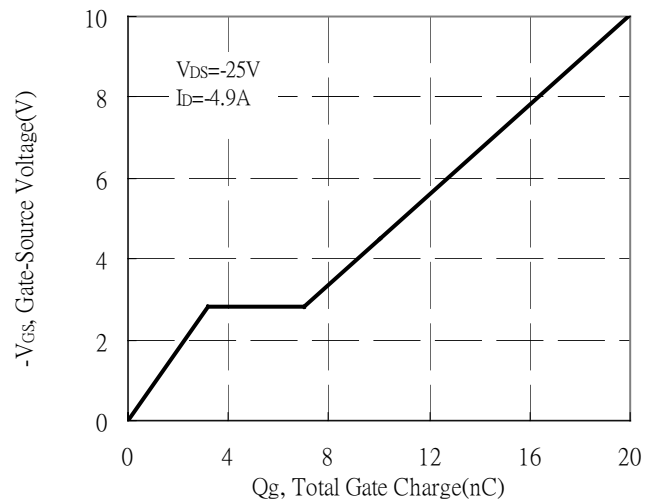
Threshold Voltage vs Junction Temperature



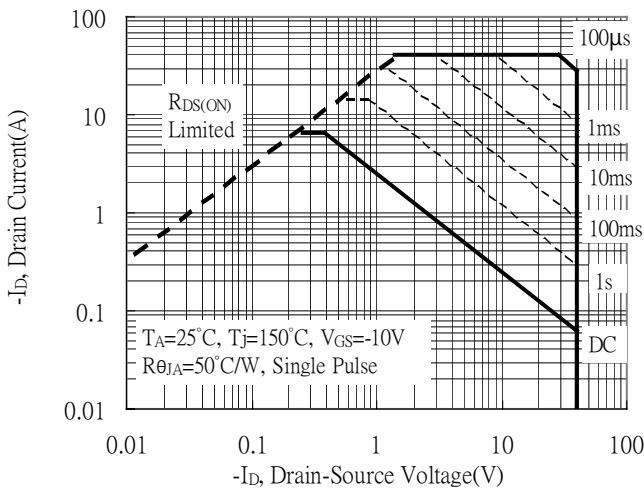
Forward Transfer Admittance vs Drain Current



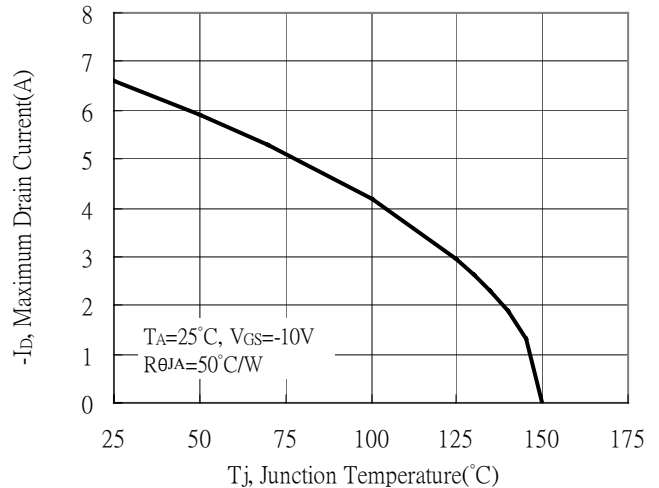
Gate Charge Characteristics



Maximum Safe Operating Area

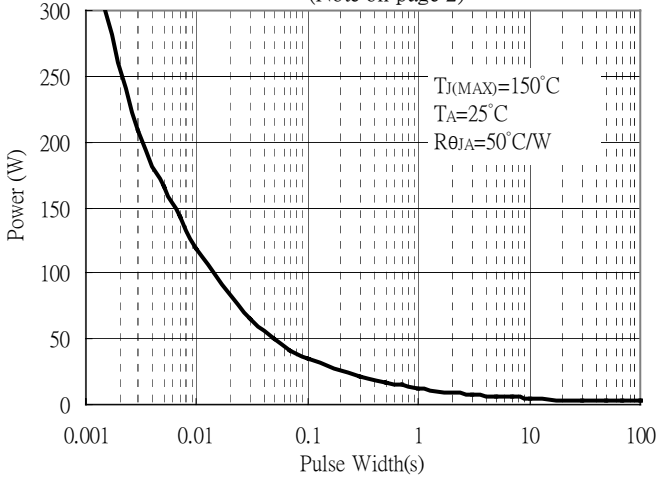


Maximum Drain Current vs Junction Temperature

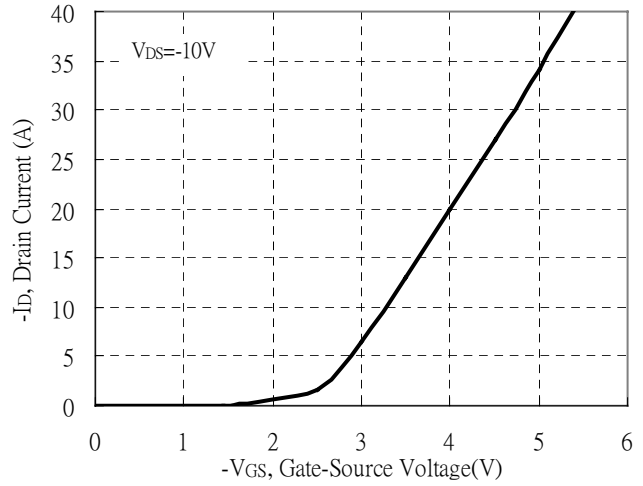


**Typical Characteristics(Cont.) : Q2(P-channel)**

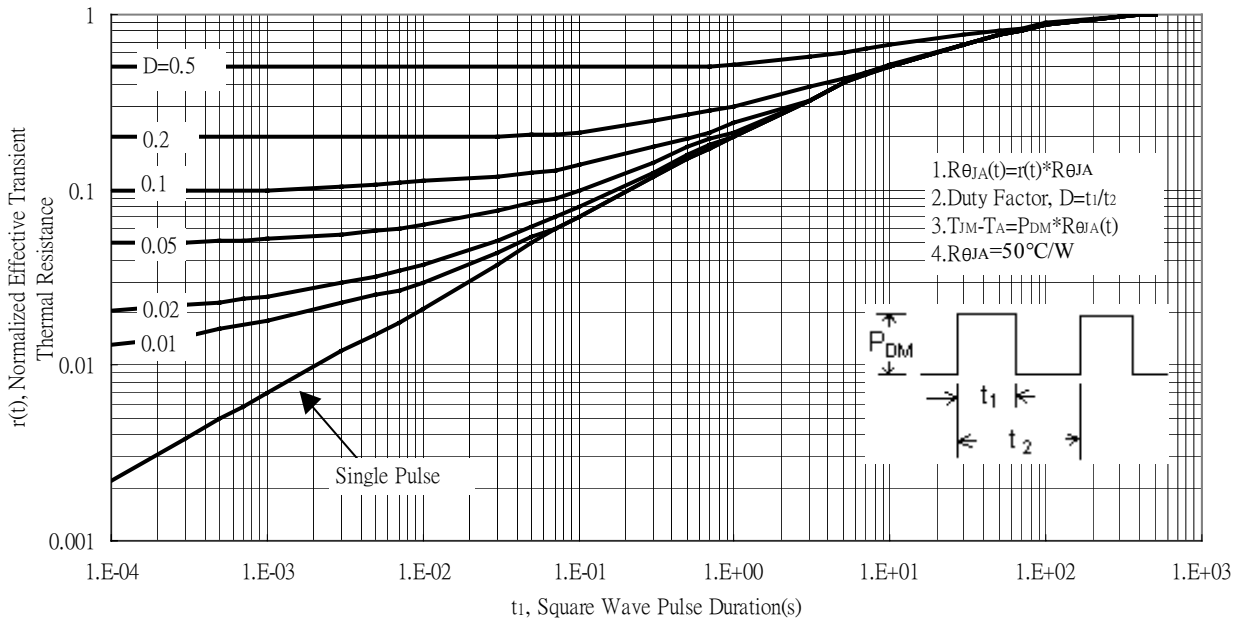
Single Pulse Power Rating, Junction to Ambient  
 (Note on page 2)



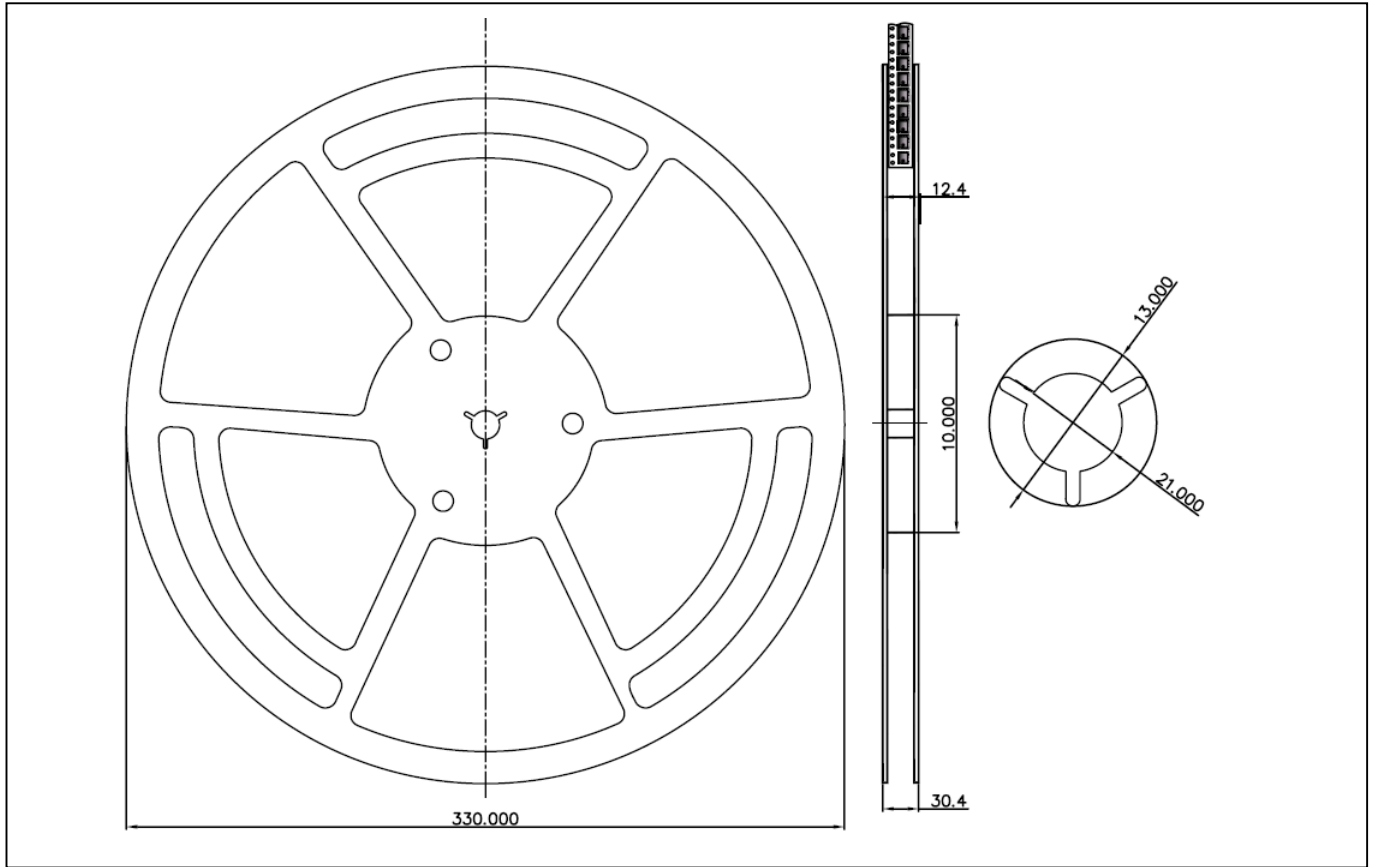
Typical Transfer Characteristics



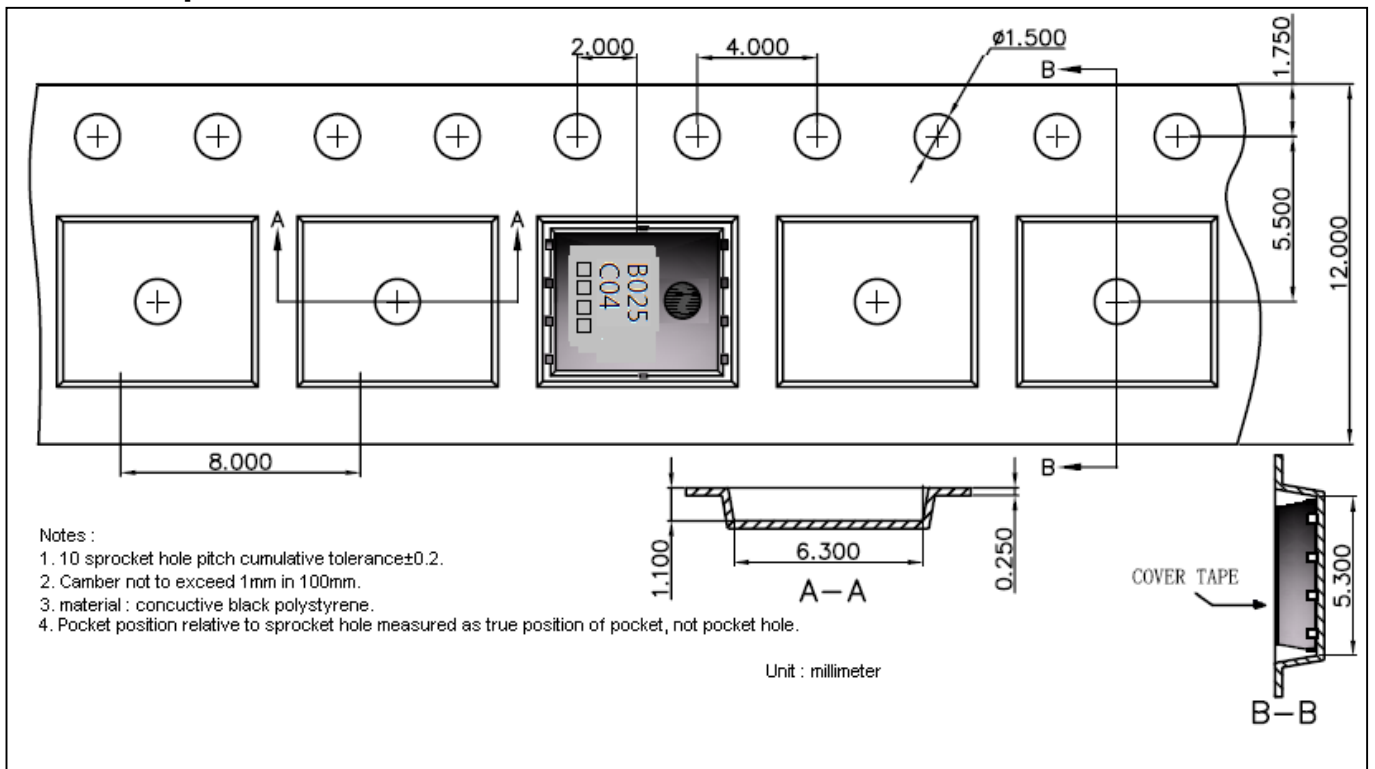
Transient Thermal Response Curves



**Reel Dimension**



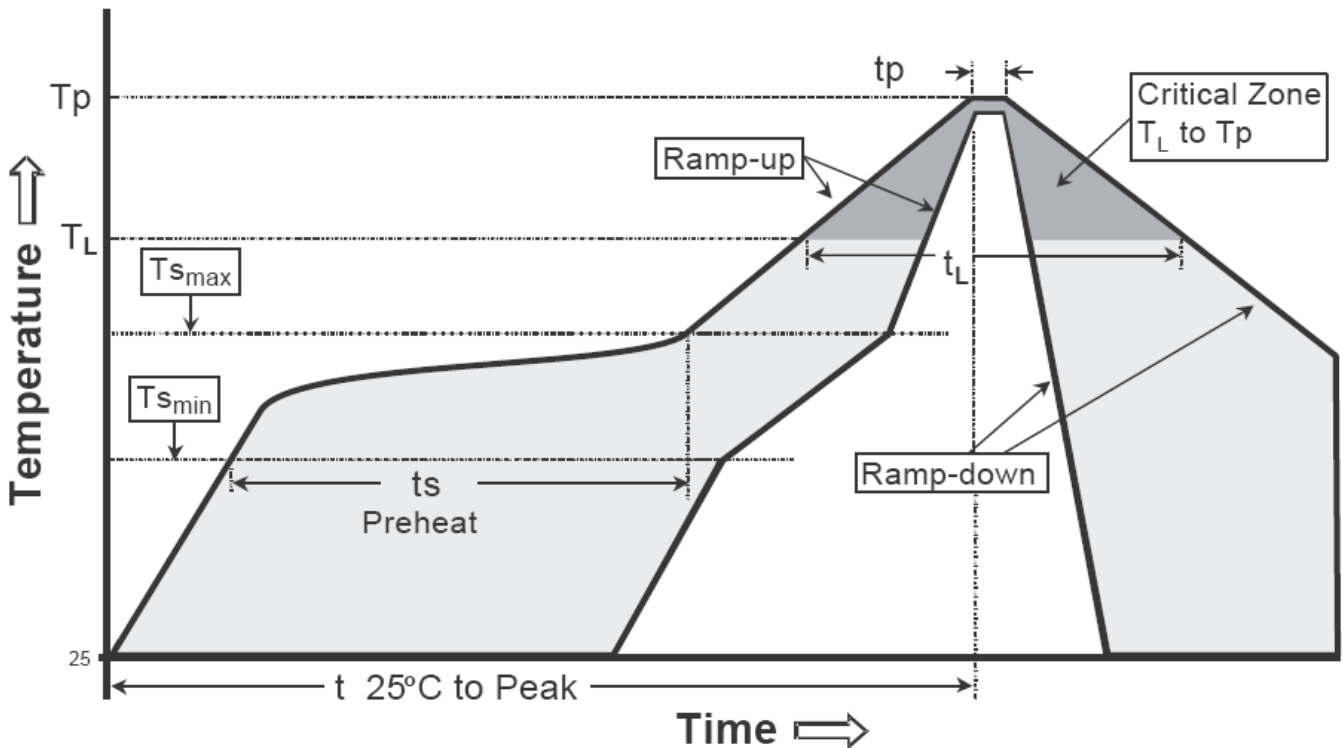
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

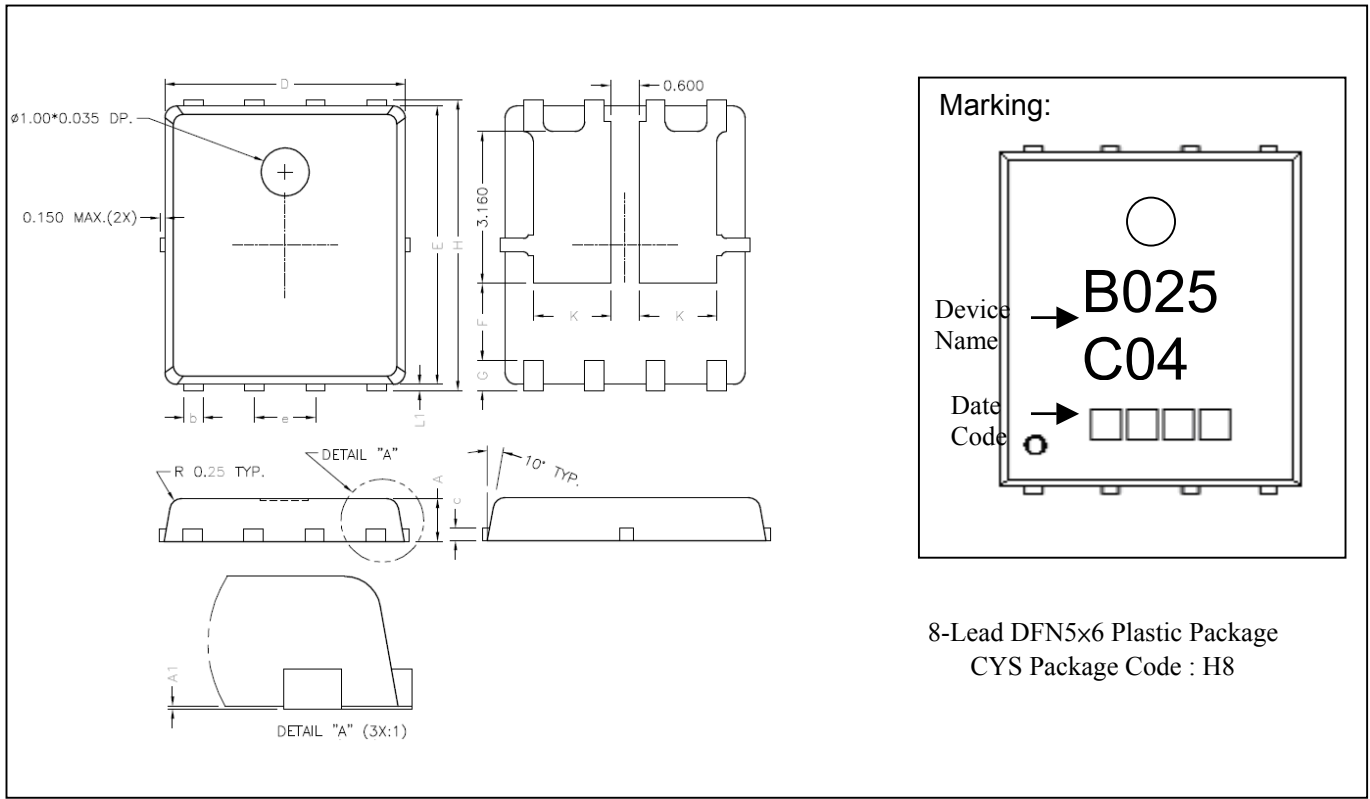
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T <sub>s min</sub> )	100°C	150°C
-Temperature Max(T <sub>s max</sub> )	150°C	200°C
-Time(t <sub>s min</sub> to t <sub>s max</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>p</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**DFN5x6 Dimension**



8-Lead DFN5x6 Plastic Package  
 CYS Package Code : H8

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.80	1.00	0.031	0.039	E	5.70	5.90	0.224	0.232
A1	0.00	0.05	0.000	0.002	e	1.27 BSC		0.050	BSC
b	0.35	0.49	0.014	0.019	H	5.95	6.20	0.234	0.244
c	0.254 REF		0.010 REF		L1	0.10	0.18	0.004	0.007
D	4.90	5.10	0.193	0.201	G	0.60 REF		0.024	REF
F	1.60 REF		0.063 REF		K	1.60 REF		0.063 REF	

Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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